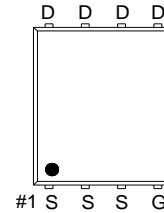
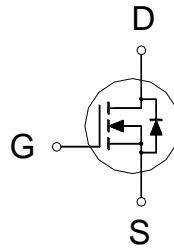




**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
60V	22.5m $\Omega$	24A



G. GATE  
D. DRAIN  
S. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ }^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	$I_D$	24	A
	$T_C = 100\text{ }^\circ\text{C}$		15	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	80	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	8	
	$T_A = 70\text{ }^\circ\text{C}$		6.8	
Avalanche Current		$I_{AS}$	26	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	33.8	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	30	W
	$T_C = 100\text{ }^\circ\text{C}$		12	
Power Dissipation <sup>3</sup>	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	3.6	W
	$T_A = 70\text{ }^\circ\text{C}$		2.3	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$		35	$^\circ\text{C} / \text{W}$
Junction-to-Ambient <sup>2</sup>	Steady-State	$R_{\theta JA}$		65	
Junction-to-Case	Steady-State	$R_{\theta JC}$		4.2	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

<sup>3</sup>The Power dissipation is based on  $R_{\theta JA} t \leq 10\text{s}$  value.

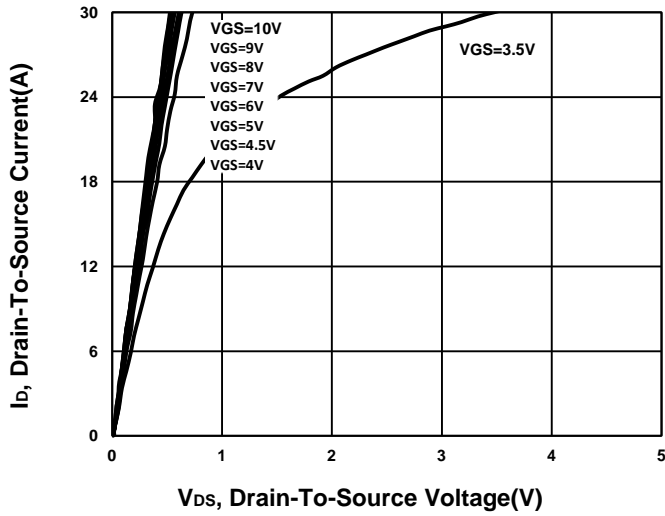
**ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.3	1.75	2.3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55 °C			10	
Drain-Source On-State Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8A		19	30	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A		16.5	22.5	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 8A		35		S
<b>DYNAMIC</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1MHz		1039		pF
Output Capacitance	C <sub>oss</sub>			123		
Reverse Transfer Capacitance	C <sub>riss</sub>			82		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz		1		Ω
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10V		23		nC
		V <sub>GS</sub> = 4.5V		13		
Gate-Source Charge <sup>2</sup>	Q <sub>gs</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> = 8A		3.4		
Gate-Drain Charge <sup>2</sup>	Q <sub>gd</sub>			7.6		
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>			38		
Rise Time <sup>2</sup>	t <sub>r</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> ≅ 8A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 6Ω		22		nS
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>			100		
Fall Time <sup>2</sup>	t <sub>f</sub>			32		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>				2.7	A
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 8A, V <sub>GS</sub> = 0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 8A, dI <sub>F</sub> /dt = 100A / μS		20		nS
Reverse Recovery Charge	Q <sub>rr</sub>				11	

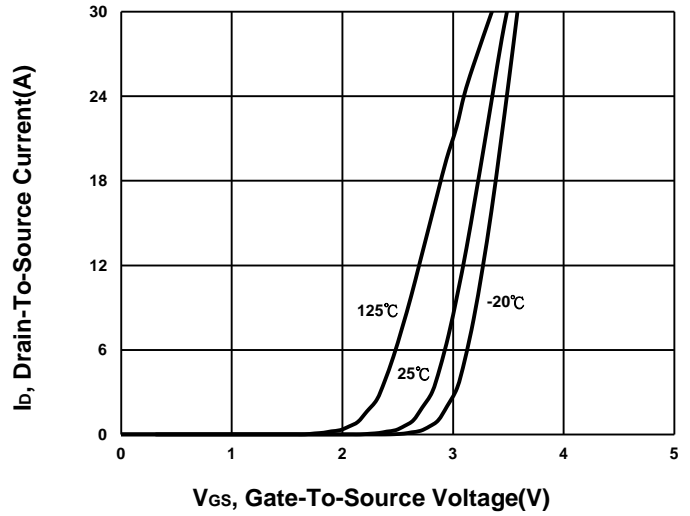
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

<sup>2</sup>Independent of operating temperature.

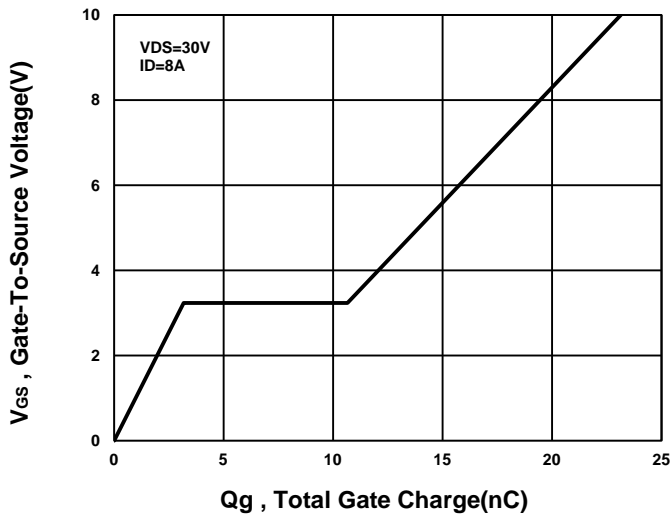
**Output Characteristics**



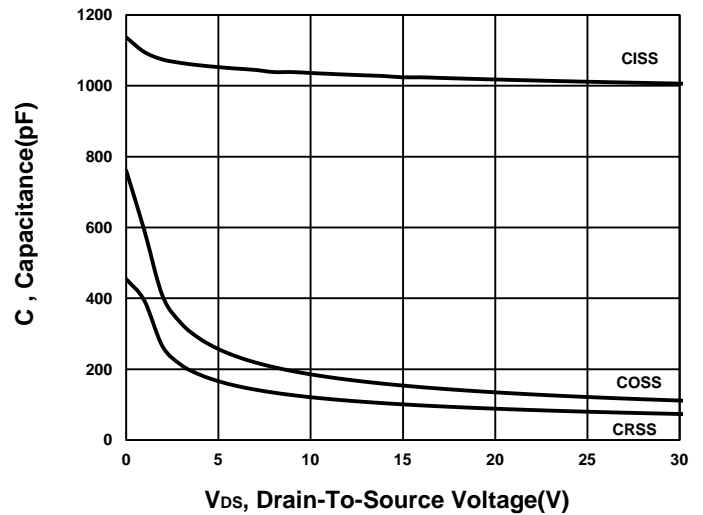
**Transfer Characteristics**



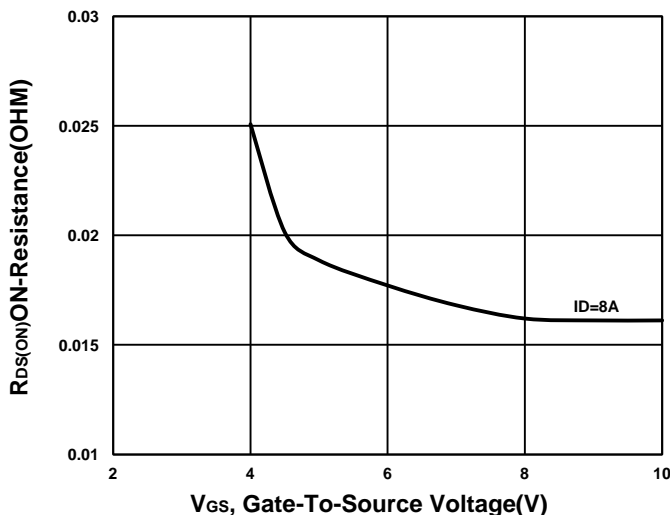
**Gate charge Characteristics**



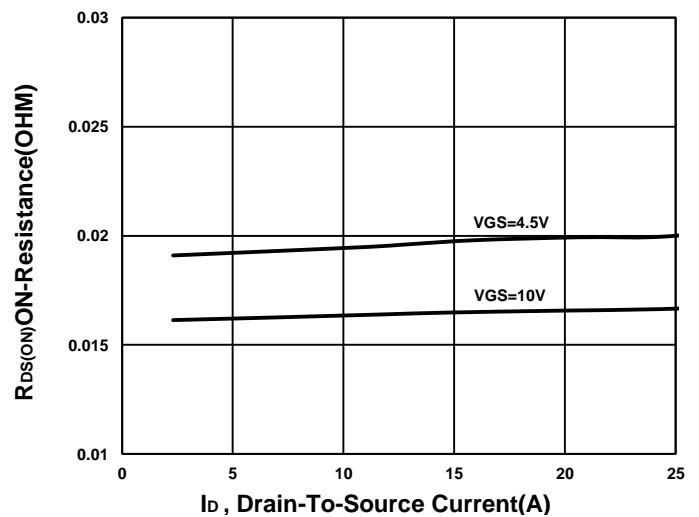
**Capacitance Characteristic**



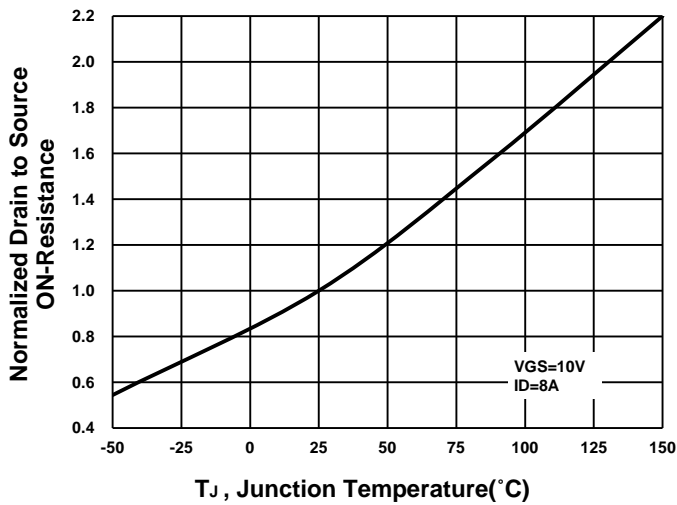
**On-Resistance VS Gate-To-Source**



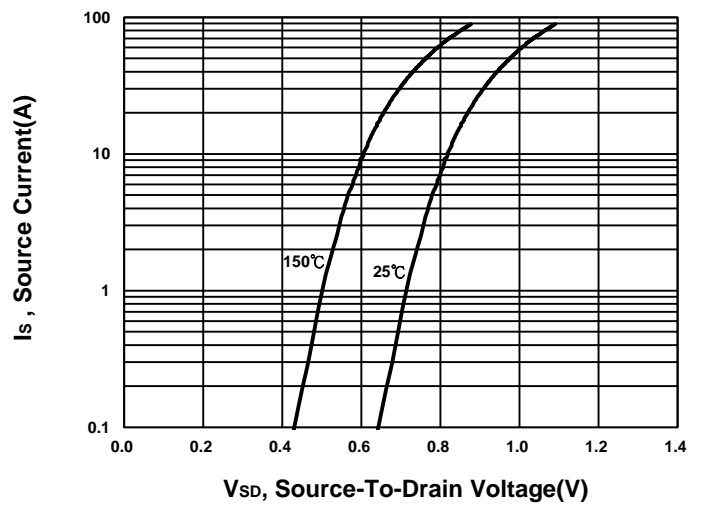
**On-Resistance VS Drain Current**



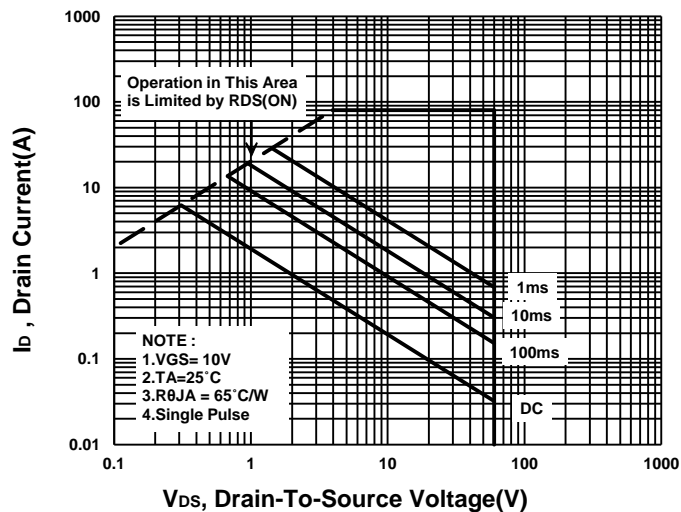
**On-Resistance VS Temperature**



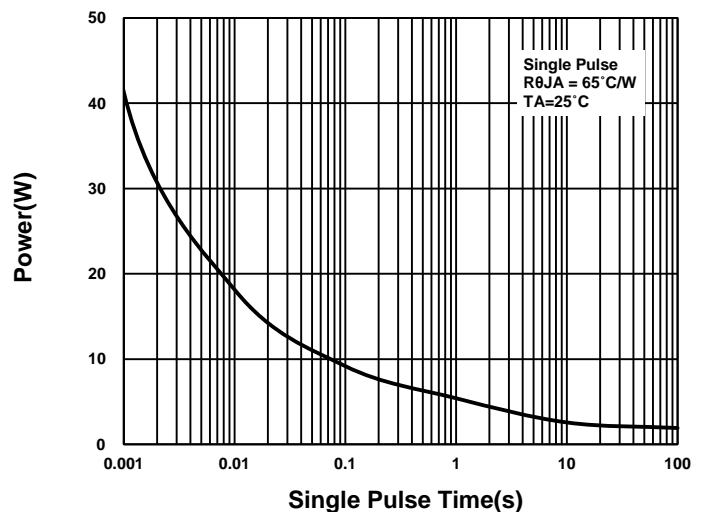
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

